

What Is Claimed Is:

- 1 1. A method for etching a mask layer, comprising steps of:
  - 2 forming a mask layer on a semiconductor substrate;
  - 3 forming a photoresist with patterns on the surface of the
  - 4 mask layer;
  - 5 forming a victim layer on the surface of the photoresist
  - 6 according to the photoresist topography, wherein the thickness
  - 7 of the victim layer is smaller than that of the photoresist, such
  - 8 that a plurality of slopes are formed on the sidewalls of the
  - 9 photoresist; and
  - 10 etching the mask layer using the photoresist and the victim
  - 11 layer with the slopes to be the etching mask.
- 1 2. The method for etching a mask layer as claimed in claim
- 2 1, wherein the mask layer is a nitride.
- 1 3. The method for etching mask layer as claimed in claim
- 2 1, wherein the thickness of the victim layer is 800~1000Å.
- 1 4. A method for etching a protecting layer for metal contact
- 2 windows, comprising steps of:
  - 3 providing a semiconductor with semiconductor elements or
  - 4 inner leads on the surface;
  - protecting layer over the inner leads.

8 forming a victim layer on the surface of the photoresist  
9 according to the photoresist topography, wherein the thickness  
10 of the victim layer is smaller than that of the photoresist with  
11 patterns, such that a plurality of slopes are formed on the  
12 sidewalls of the photoresist; and

13 etching the protecting layer to form a plurality of metal  
14 contacting windows using the photoresist and the victim layer  
15 with the slopes to be the etching mask.

1 5. The method for etching a protecting layer for metal  
2 contact windows as claimed in claim 4, wherein the protecting  
3 layer is nitride.

1 6. The method for etching a protecting layer for metal  
2 contact windows as claimed in claim 4, wherein the victim layer  
3 is an anti-reflection coating layer.

1 7. The method for etching a protecting layer for metal  
2 contact windows as claimed in claim 4, wherein the thickness of  
3 the victim layer is 800~1000Å.

1 8. The method for etching a protecting layer for metal  
2 contact windows as claimed in claim 4, wherein the plurality of  
3 metal contacting windows are pad regions and fuse regions  
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